# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

The **ASI UHBS60-2** is Designed for

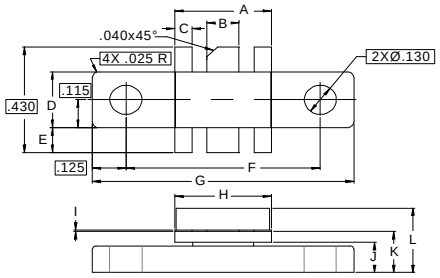
## FEATURES:

- 
- 
- ***Omnigold***™ Metalization System

## MAXIMUM RATINGS

| | |
|---|---|
| $I_C$ | 9.0 A |
| $V_{CBO}$ | 50 V |
| $V_{CEO}$ | 26 V |
| $V_{CES}$ | 50 V |
| $V_{EBO}$ | 4.0 V |
| $P_{DISS}$ | 190 W @ $T_C$ = 25 $^{O}$C |
| $T_J$ | -65 $^{O}$C to +200 $^{O}$C |
| $T_{STG}$ | -65 $^{O}$C to +150 $^{O}$C |
| $\theta_{JC}$ | 0.9 $^{O}$C/W |

## PACKAGE STYLE .230 6L FLG




| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|---|---|---|
| A | .355 / 9.02 | .365 / 9.27 |
| B | .115 / 2.92 | .125 / 3.18 |
| C | .075 / 1.91 | .085 / 2.16 |
| D | .225 / 5.72 | .235 / 5.97 |
| E | .090 / 2.29 | .110 / 2.79 |
| F | .720 / 18.29 | .730 / 18.54 |
| G | .970 / 24.64 | .980 / 24.89 |
| H | .355 / 9.02 | .365 / 9.27 |
| I | .004 / 0.10 | .006 / 0.15 |
| J | .120 / 3.05 | .130 / 3.30 |
| K | .160 / 4.06 | .180 / 4.57 |
| L | .230 / 5.84 | .260 / 6.60 |

**ORDER CODE: ASI10673**

## CHARACTERISTICS $T_C$ = 25 $^{O}$C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|---|---|---|---|---|---|
| $BV_{CBO}$ | $I_C$ = 50 mA | 50 | | | V |
| $BV_{CES}$ | $I_C$ = 50 mA | 50 | | | V |
| $BV_{CEO}$ | $I_C$ = 50 mA | 26 | | | V |
| $BV_{EBO}$ | $I_E$ = 10 mA | 3.0 | | | V |
| $I_{CES}$ | $V_{CE}$ = 20 V | | | 10 | mA |
| $I_{CBO}$ | $V_{CB}$ = 30 V | | | 5 | mA |
| $h_{FE}$ | $V_{CE}$ = 5.0 V  $I_C$ = 1.0 A | 20 | | 100 | --- |
| $C_{ob}$ | $V_{CB}$ = 24 V  f = 1.0 MHz | | | 75 | pF |
| $P_G$ | $V_{CE}$ = 24 V  $P_{OUT}$ = 60 W  f = 960 GHz | 7.0 | | | dB |
| $\eta_C$ | | | 50 | | % |

ADVANCED SEMICONDUCTOR, INC.
7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1200 • FAX (818) 765-3004



*Specifications are subject to change without notice.*